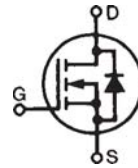


HiPerFET™

Power MOSFET

Q2-Class

IXFK40N50Q2

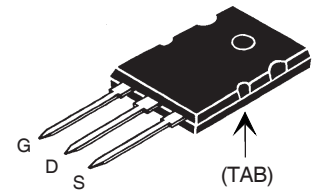


N-Channel Enhancement Mode
 Avalanche Rated, High dv/dt , Low Q_g
 Low intrinsic R_g , low t_{rr}

$$\begin{aligned} V_{DSS} &= 500V \\ I_{D25} &= 40A \\ R_{DS(on)} &\leq 160m\Omega \\ t_{rr} &\leq 250ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	40	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	160	A
I_A	$T_C = 25^\circ\text{C}$	40	A
E_{AS}	$T_C = 25^\circ\text{C}$	2.5	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	560	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.063 in) from case for 10s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		10	g

TO-264 (IXFK)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- Double metal process for low gate resistance
- International standard package
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- Pulse generation
- Laser drivers

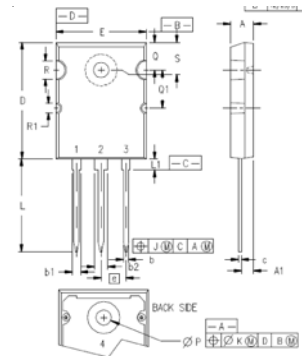
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{mA}$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			160 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1	15	28	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		4850	pF
C_{oss}			680	pF
C_{rss}			170	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		17	ns
t_r			13	ns
$t_{d(off)}$			42	ns
t_f			8	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		110	nC
Q_{gs}			25	nC
Q_{gd}			50	nC
R_{thJC}			0.22	$^\circ\text{C/W}$
R_{thCK}		0.15		$^\circ\text{C/W}$

TO-264 (IXFK) Outline



- 1 - GATE
- 2, 4 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			40 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			160 A
V_{SD}	$I_F = I_s, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 25\text{A}, -di/dt = 100\text{A}/\mu\text{s}, V_R = 100\text{V}$		1	250 ns
Q_{RM}			9	μC
I_{RM}				A

Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

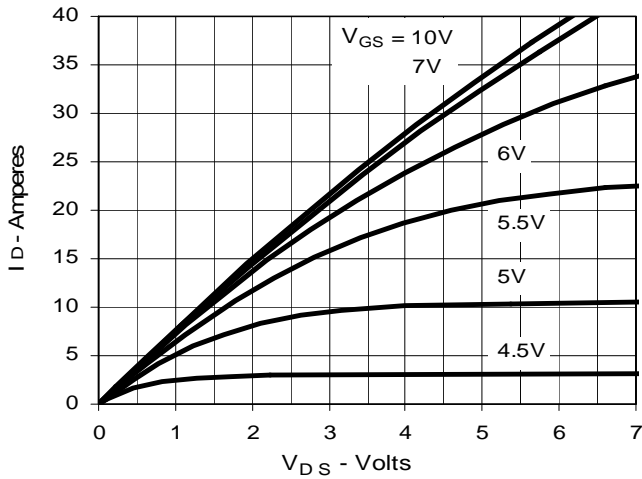
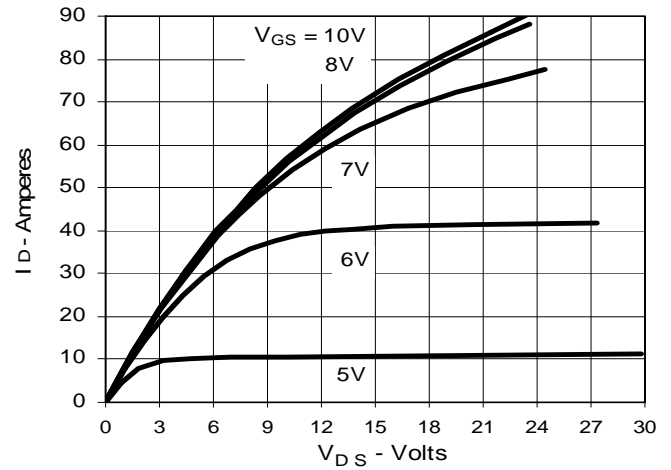
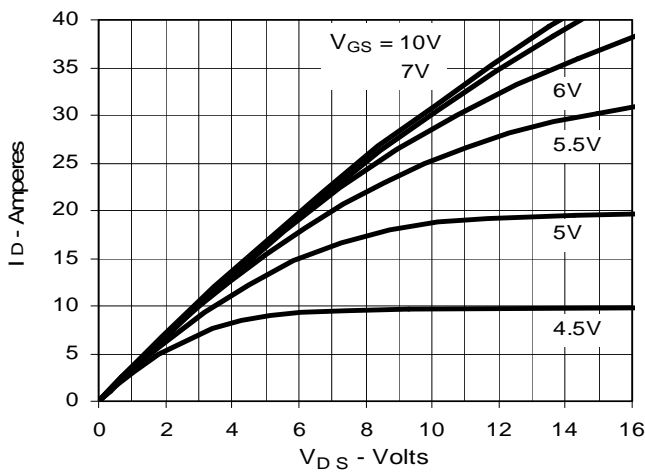
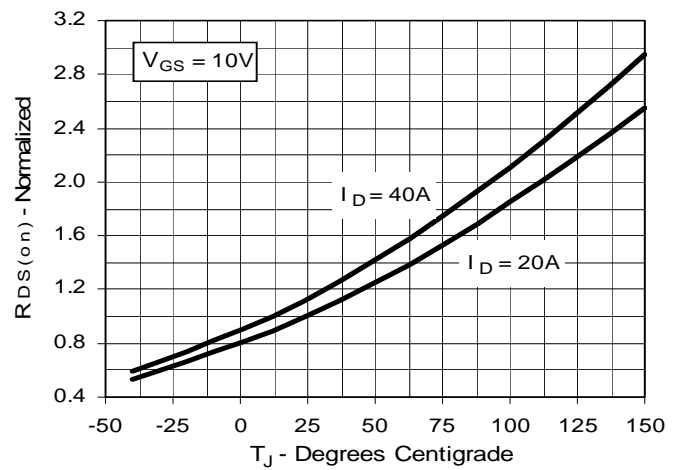
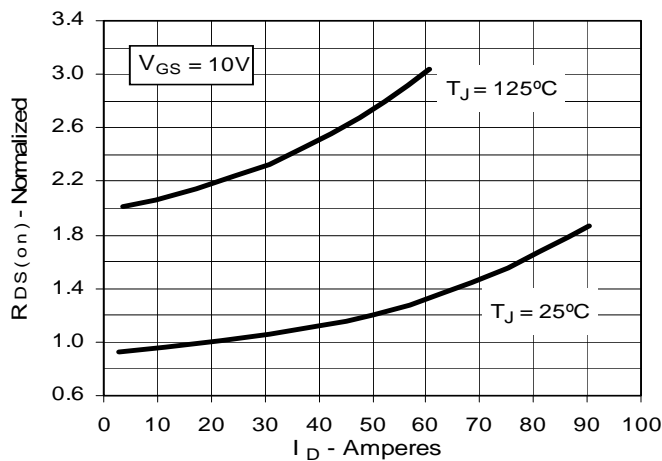
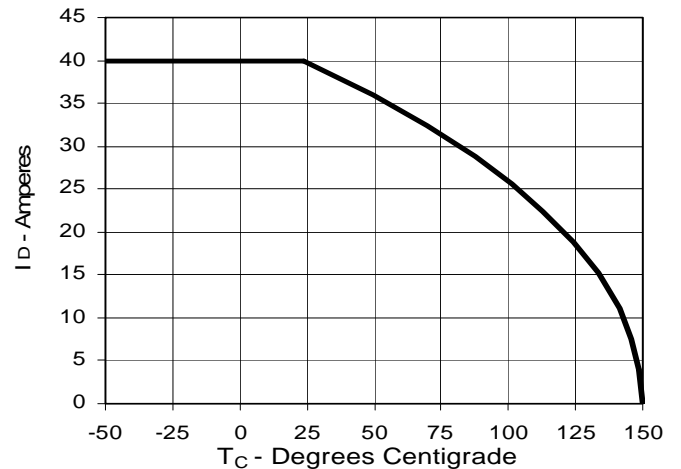
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value
vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value
vs. I_D**

Fig. 6. Drain Current vs. Case Temperature


Fig. 7. Input Admittance

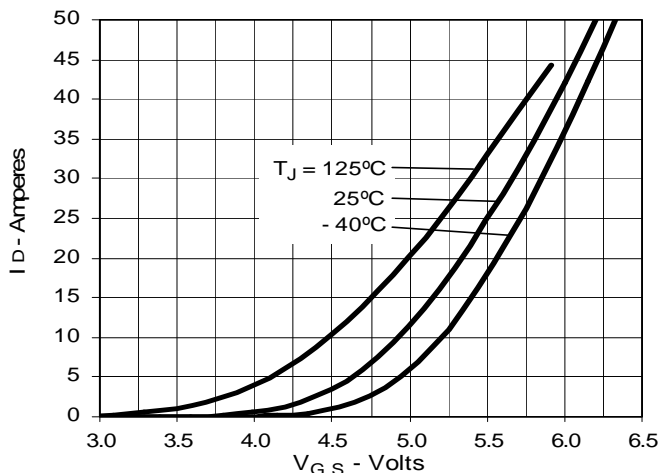


Fig. 8. Transconductance

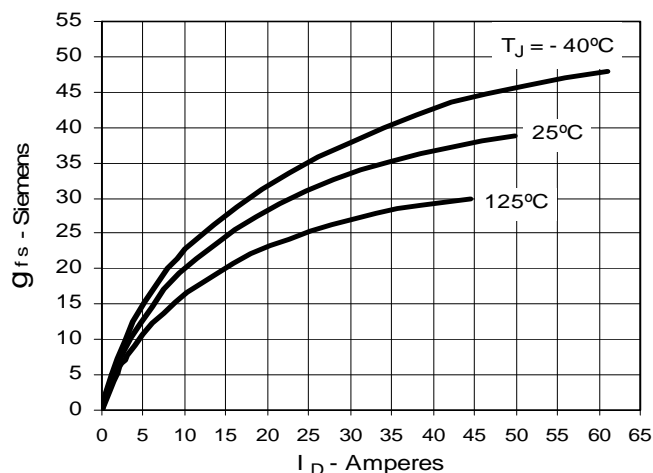


Fig. 9. Source Current vs. Source-To-Drain Voltage

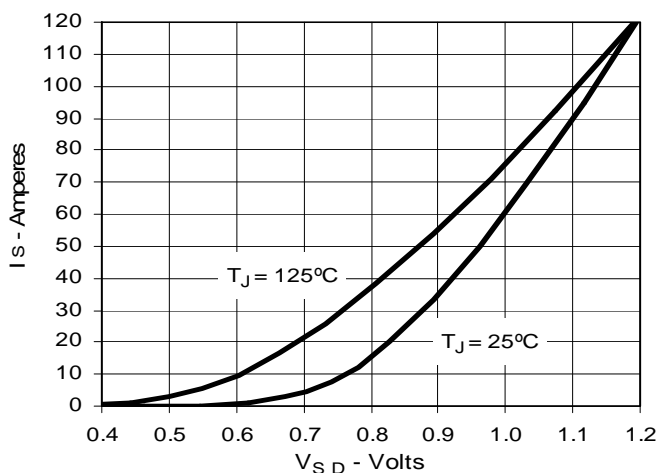


Fig. 10. Gate Charge

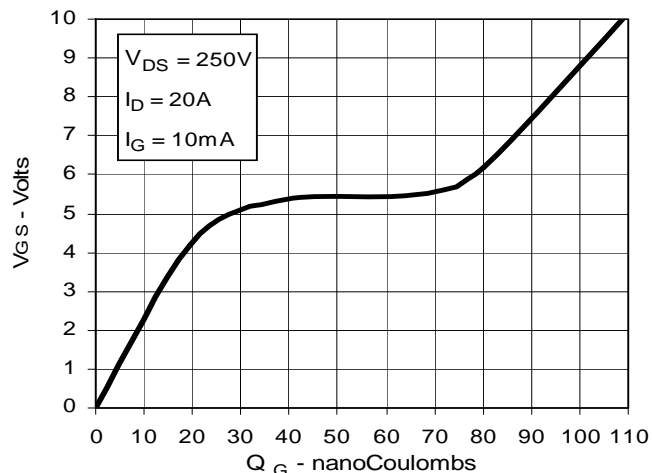


Fig. 11. Capacitance

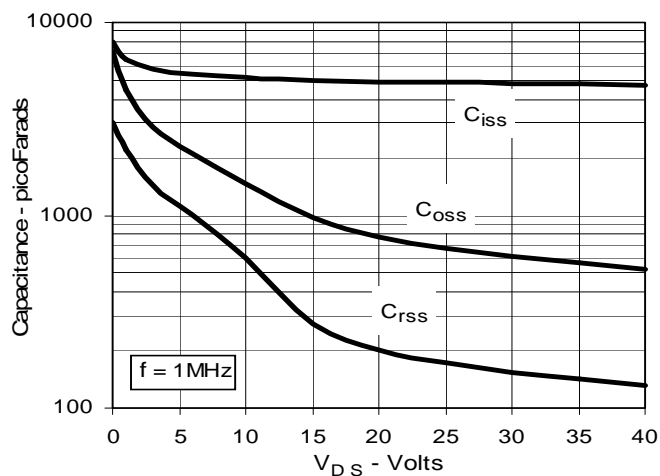
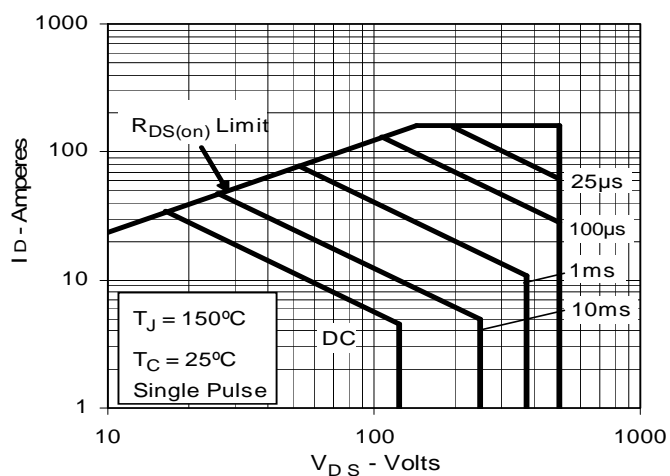


Fig. 12. Forward-Bias Safe Operating Area



IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 13. Maximum Transient Thermal Impedance

